

[Type of document] Abstract

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[Problem] The invention provides a method for manufacturing a semiconductor device with which an impurity introduction region and a 5 positioning mark region can be formed aligned, based on a common insulating film pattern.

[Means to solve] The method for manufacturing a semiconductor device includes an insulating film pattern formation step; a first photosensitive pattern formation step of forming, on the insulating film pattern, a first 10 photosensitive pattern with an aperture that exposes a positioning mark region, the first photosensitive pattern covering an impurity introduction region; a level difference formation step of forming in the semiconductor substrate, at the aperture formed in the insulating film pattern, a level difference for adjusting a position of the photomask at the positioning mark 15 region; a first photosensitive pattern removal step of removing the first photosensitive pattern; and an impurity introduction step of introducing the impurities through the aperture formed in the insulating film pattern into the impurity introduction region.

[Selected figure] FIG 1